Electron and Hole Spin Splitting and Photogalvanic E ect in Quantum Wells

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A theory of the circular photogalvanice ect caused by spin splitting in quantum wells is developed. Direct interband transitions between the hole and electron size-quantized subbands are considered. It is shown that the photocurrent value and direction depend strongly on the form of the spin-orbit interaction. The currents induced by structure, bulk-, and interface-inversion asymmetry are investigated. The photocurrent excitation spectra caused by spin splittings in both conduction and valence bands are calculated.

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I. INTRODUCTION

The spin properties of carriers have attracted much attention in recent years due to rapidly developed spintronics dealing with the manipulation of spin in electronic devices. The rst idea was put forward by D atta and D as, who proposed a spin eld-e ect transistor. Its work is based on a change of the Rashba eld in semiconductor heterostructures, caused by structure inversion asymmetry (SIA).

The promising materials for spintronics are III-V semiconductor quantum wells (QW s) whose spin properties are well-documented and can be controlled by advanced technology. However, in addition to the Rashba spin-orbit interaction, other elective magnetic elds act on carriers in zinc-blende heterostructures. This is, rst, the so-called Dresselhaus eld caused by bulk inversion asymmetry (BIA). 4,5,6,7,8,9 It is present in QW smade of semiconductors without inversion center.

Second, there is the spin-orbit interaction produced by the interface inversion asymmetry (IIA). It has been established that the single-interface symmetry allows heavy-light hole mixing at zero in-plane wave vector. In the spin splitting in both valence and conduction bands at nonzero wave vector. The structure of the corresponding linear in the wave vector contribution to the electron elective Hamiltonian coincides with that due to BIA. In the following both contributions, BIA and IIA, are considered together as a generalized BIA eld.

Both SIA and BIA give rise to many spin-dependent phenomena in QW s, such as an existence of beats in the Shubnikov-de Haas oscillations, spin relaxation, splitting in polarized Raman scattering spectra, and positive anomalous magnetoresistance. Spin splittings and relaxation times have been extracted from these experiments. However, in (001)-grown QW s, the SIA and BIA spin-orbit interactions result in the same dependences of spin splittings and spin relaxation times on the wave vector. Therefore it is impossible to determine the nature for the spin splitting at low wave vectors. Only in the simultaneous presence of both BIA and SIA of comparable strengths, one can observe new elects, see Ref. 25 and references therein. However the latter situation is rare

in real systems because it requires a special structure design. Usually SIA and BIA cannot be distinguished in experiments.

In this work, the other spin-dependent phenom enon is investigated which is essentially dierent from the ones mentioned above. This is the Circular Photo-Galvanic E ect which is a conversion of photon angular momentum into a directed motion of charge carriers. The result is an appearance of electric current under absorption of a circularly-polarized light. The photocurrent reverses its direction under inversion of the light helicity. M icroscopically, the circular photocurrent appears owing to a coupling between orbital and spin degrees of freedom. In sem iconductors the coupling is a consequence of the spinorbit interaction. In two-dim ensional system s, the circular photogalvanic e ect can be caused by both Rashba and D resselhaus e ective magnetic elds. In this paper we show that SIA and BIA result in experim entally distinguishable photocurrents.

The recently started activity on circular photogalvanics in QW sattracted much attention. The photocurrents induced by both SIA and BIA have been investigated. The circular photocurrent has been mostly studied under intraband transitions induced by infrared or far-infrared excitations. However it is important to extend studies on the optical range where the elect is expected to be much stronger. In this case, the photocurrent appears due to interband transitions.

In the present work, the theory of the interband circular photogalwanic e ect in QW s is developed, and the photocurrent spectra are calculated.

II. GENERAL THEORY

In the absence of a spin-orbit interaction, two states with the same wave vector k in the same size-quantized subband, jli and j2i, are degenerate. In a sym metrical QW, the electron envelope functions of these states can be chosen in the form

$$j_e i = \exp(ik)$$
)'(z)"; $j_e i = \exp(ik)$)'(z)#; (1)

where z is the growth direction, is the electron position in the plane of QW, and " and # are the spin-up and

spin-down functions. For odd (even) subbands of size-quantization, '(z) = '(z), respectively.

The two degenerate hole states with the wave vector k can be chosen as $\mathsf{sym}\,\mathsf{m}$ etrical and antisym m etrical with respect to the mirror rejection in the plane located in the middle of the QW. The wave function for the $\mathsf{sym}\,\mathsf{m}$ etrical state has the form 29

and the antisymmetrical wave function $\mathcal{P}_h i$ can be obtained from $Jl_h i$ by applying the operations of time and space inversion. Here $u_{3=2}$, $u_{1=2}$ are the Bloch functions at the top of the valence band, $_+$ and $_-$ are respectively, even and odd functions of coordinate z, $_+^{30}$ and $_ _k$ is the angle between [100] and k:

tan
$$k = k_y = k_x$$
:

Spin-orbit interaction in QW s is described by the Hamiltonian which has the following form in the basis of two states ili and 2i

$$H(k) = (k):$$
 (3)

Here $_{\rm x}$, $_{\rm y}$ are the Paulim atrices acting on the states jli and j2i. Thee ective k-dependent magnetic eld B_{eff} /

(k) is determined by the type of inversion asymmetry. In the presence of the spin-orbit interaction (3), the

- two eigenstates with a given wave vector k are split by = 2j (k)j. We denote these states by the index m =
- . Their envelope functions in size-quantized subbands can be chosen in the form

where the phase k is given by

tan
$$k = y = x$$
:

Let us now consider optical excitation of a QW by circularly-polarized light (see Fig. 1). Here we investigate the photocurrent arising due to asym metry of the carrier distribution in the k-space at the moment of creation. It is dierent from another photocurrent caused by carrier momentum redistribution during the process of spin relaxation. The latter, so-called spin-galvanice ect, was considered in Refs. 31 and 28. These two photocurrents can be separated in the time-resolved experiments: after switching-o the light source, the former decays with the momentum relaxation time while the latter disappears within the spin relaxation time.

The electric current is expressed in terms of the velocity operators and spin density matrices for electrons and holes as follows

$$j = e^{X \quad h}$$
 $Tr v^{(e)}(k)^{(e)}(k) \quad v^{(h)}(k)^{(h)}(k)^{(h)}; \quad (5)$

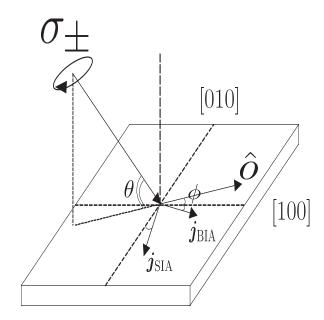


FIG. 1: SIA - and BIA - induced photocurrents appearing under oblique incidence of circularly-polarized light.

where e is the electron charge.

D ensity-m atrix equations taking into account both direct optical transitions and elastic scattering give the following expressions for linear in the light intensity values entering into Eq.(5)

$$_{nn^{\circ}}^{(e;h)} = \frac{X}{h_{e;h}} M_{nn}M_{nn^{\circ}} [(E_n + E_n + E_n + 1)]$$

$$+ (E_{n^{\circ}} + E_n + 1)] :$$

Here $_{\rm e}$ and $_{\rm h}$ are the relaxation times of electrons and holes (here we assume isotropic scattering), h! is the photon energy, M $_{\rm nn}$ (k) is them atrix element of the direct optical transition between the states n and n, and the energy dispersions E $_{\rm e,h}$ (k) are reckoned inside the bands.

Spin splittings of electron or hole subbands both give rise to the circular photogalvanice ect. The corresponding contributions to the current are independent, therefore we consider the cases of electron and hole spin splittings separately.

III. ELECTRON SPIN-SPLITTING INDUCED PHOTOCURRENT

Here we take into account spin splitting in the conduction band. In QW s, the spin-orbit interaction Eq. (3) is described by the linear in the wave vector Ham iltonian

$$_{i}\left(k\right) =$$
 $_{il}k_{l}$: (7)

C ubic in k corrections do not result in a circular photogalvanic e $\,$ ect, therefore we do not consider them $\,$ below .

Tensor is determ ined by the sym m etry of the Q W . As m entioned in the Introduction, in structures with a zinc-blende lattice, there is a contribution due to B IA and IIA

known as the D resselhaus term . For (001)-grown QW s, it has two non-zero components, namely

$$_{xx} = _{yy} _{BIA};$$
 (8)

where x k [100] and y k [010].

SIA appears due to di erence of the right and left barrier heights of the QW, electric elds applied along z direction, etc. It leads to an additional contribution to the spin-orbit H am iltonian, the so-called R ashba term:

$$xy = yx$$
 $SIA :$ (9)

The velocity matrix elements calculated on the wave functions (4) taking into account the spin-orbit corrections (3), are given by

$$\begin{split} v_{i}^{(e)} & = \frac{hk_{i}}{m_{e}} + \frac{m}{h} \left(\sum_{x_{i}} \cos k_{x_{i}} + \sum_{y_{i}} \sin k_{x_{i}} \right) + \frac{m}{h} \left(\sum_{y_{i}} \cos k_{x_{i}} + \sum_{x_{i}} \sin k_{x_{i}} \right) \left(1 - \sum_{x_{i}} k_{x_{i}} \right) ; \\ v_{i}^{(h)} & = \frac{k_{i}}{k} v_{h} (k); \quad v_{h} (k) = \frac{1}{h} \frac{dE_{h}(k)}{dk}; \end{split} \tag{10}$$

where m $_{\rm e}$ is the electron e ective m ass.

Calculations show that all odd Fourier harm onics of $^{(e;h)}$ (k) entering into (5) are proportional to the follow-ing part of the sum

$$[W \sin(k_k + 2_k + k_k +$$

Here $P_{\rm circ}$ is the circular polarization degree, and are the spherical angles of the light polarization vector (see Fig. 1), p is the interband momentum matrix element, A_0 is the light wave amplitude, m_0 is the free electron mass, and

$$Q = dz'(z)$$
 (12)

The upper (lower) sign in Eq. (11) corresponds to excitation into the odd (even) electron subbands.³⁰

The characteristic spin splittings are usually very small, therefore we consider a linear in regime. In this approximation, SIA and BIA give independent contributions into the photocurrent

$$j(!) = j_{SIA}(!) + j_{BIA}(!);$$
 (13)

where $j_{S\,IA}$ and $j_{B\,IA}$ are linear in $_{S\,IA}$ and $_{B\,IA}$, respectively. A ssum ing the splitting ! 0 and calculating the reduced density of states, we obtain from Eqs. (5) – (12) the expressions for the interband circular photocurrents:

$$j_{i}(!) = \lim_{h \to 0} P_{circ} \frac{epA_0}{m_0 hc}^2 \frac{e}{h} G(k_!)$$
: (14)

Here i;l=x;y, and δ is a projection of the unit vector along the light propagation direction on the QW plane (see Fig. 1). The wave vector of the direct optical transition, $k_{!}$, satis es the energy conservation law

$$E_{e}(k_{!}) + E_{h}(k_{!}) = h! E_{r};$$
 (15)

where $E_e(k) = h^2 k^2 = 2m_e$ is the electron energy without spin-orbit corrections, and $E_h(k)$ stands for the hole dispersion, calculated in the spherical approximation.

We study the elects linear in , therefore Eq. (14) is valid at h! E_g^{QW} $k_!$, where $E_g^{QW} = E_g + E_{e1}$ (0) + E_{h1} (0) is the fundamental energy gap corrected for the energies of size-quantization. However for real systems, the theory is valid even near the absorption edge.

The frequency dependence of the photocurrent is given by the function G (k)

$$G(k) = \frac{k}{v(k)} \frac{d}{dk} \frac{F(k)u(k)}{v(k)} + \frac{F(k)}{v(k)} \frac{u(k)}{v(k)}$$
 2; (16)

w here

$$F(k) = k[N(k)Q(k)W(k)]^{2} e(k);$$
 (17)

$$v(k) = \frac{hk}{m_e} + v_h(k); u(k) = \frac{hk}{m_e} + v_h(k) \frac{h(k)}{h(k)}$$
 (k):

The rst term in Eq. (16) appears because the direct transitions to the upper (lower) spin branch take place at a wave vector slightly sm aller (larger) than k_1 , and the second term occurs because the two electron spin states with the same k have di erent velocities.

The factor (k) depends on the form of a spin-orbit interaction. It follows from Eqs. (8), (9) that, for the BIA-induced spin-orbit interaction, $_{\rm k}$ = $_{\rm k}$, while, for SIA-dom inance, $_{\rm k}$ = $_{\rm k}$ = 2. Therefore one has

$$_{BIA} = 1;$$
 $_{SIA} = 1$ 1=W (k): (18)

The dierence appears because in the BIA-case the term s with W in Eq. (11) are the third harm onics of $_{\rm k}$ and, hence, do not contribute to the current. This means that BIA and SIA create dierent current distributions of optically-generated electrons.

This di erence gives rise to non-equal frequency dependences of the photocurrent. It is dram atic at the absorption edge, when h! $E_g^{Q\,W}$. For the ground hole subband W $_+$ (k) k^2 , and hence

$$j_{BTA}$$
 (h! f_{B}^{W})²; j_{STA} h! f_{B}^{W} : (19)

This conclusion opens a possibility to distinguish experimentally which kind of asymmetry, BIA or SIA, is dominant in the structure under study. This could be done by studying the power, quadratic or linear, in the dependence of the circular photocurrent on the light frequency near the absorption edge. At higher photon energies, the spectra are also dierent due to k-dependence of the functions W [see Eq. (18)].

IV. HOLE SPIN-SPLITTING INDUCED PHOTOCURRENT

In this section we calculate the circular photocurrent which arises due to the spin splitting in the valence size-quantized subbands. The split hole states have wave functions Eq. (4), the two degenerate states in the conduction band are given by Eq. (1).

SIA and BIA result in the hole spin splitting as well as for electrons. Below we consider both cases and derive the expressions for circular photocurrents.

A. SIA -induced circular photocurrent

SIA is described by the hole H am iltonian 32,33 which has the following form in the basis $u_{3=2}$, $u_{1=2}$, $u_{1=2}$, $u_{3=2}$

$$H(k) = i k \begin{bmatrix} 0 & 0 & 0 & 1 \\ 0 & 0 & 0 & 0 \\ B & 0 & 0 & e^{i \times 0} & 0 \\ 0 & 0 & e^{i \times 0} & 0 & 0 \\ 0 & 0 & 0 & 0 \end{bmatrix}$$
(20)

In a weak electric eld applied along the growth direction, the k-independent coe cient is proportional to its strength.

In the basis $jl_h i$, $j2_h i$ the Ham iltonian Eq. (20) has the form of Eq. (3) with

$$_{x} + i_{y} = h2_{h} H J_{h} i = iA \exp(3i_{k});$$
 (21)

w here

The splitting equals to = $2 \frac{\pi}{4} (k) \frac{\pi}{3}$ and the phase k = 3 + k = 2.

At k! 0, for the h1 subband one has k^3 . For the l1 subband, the H am iltonian in the basis exp $(2i_k)_2h_i$, exp $(2i_k)_3h_i$ has the form

$$H(k) = (x_x k_y y_x k_x);$$

i.e. it is similar to the SIA-Ham iltonian for electrons, Eqs. (7), (9). The splitting in this case is linear in k. In real experiments, the hole wave vector may be large, therefore we take into account the nonparabolicity elects and allow explicit k-dependence A (k) in Eq. (21).

Calculating the photocurrent, we arrive at the expression (14) with the k-dependent tensor given by

$$_{xy}(k) = _{yx}(k) = \frac{dA}{dk}$$
 (23)

and with the following function G (k) which determine the photocurrent excitation spectrum

$$G(k) = \frac{k}{(k)v(k)} \frac{d}{dk} \frac{F(k)u(k)}{v(k)} + \frac{F(k)}{v(k)} \frac{u(k)}{v(k)} 2 + 1 + \frac{1}{W(k)} 1 \frac{3}{(k)} :$$

Here F, u and v are given by Eq. (17) with = 1 1=W and interchange $_{\rm e}$ \$ $_{\rm h}$. The factor

$$(k) = \frac{d \ln A}{d \ln k}$$
 (25)

Atk! 0, = 3 for the h1-subband and = 1 for the l1-subband. The edge behavior of the spectrum is governed by the h1! el transitions and follows the quadratic law

$$j_{SIA}$$
 (h! f_{S}^{W})²: (26)

B. BIA - and IIA -induced circular photocurrent

IIA is described by the interface term in the H am iltonian $^{11},^{12},^{13},^{33},^{34}$

$$H_{IIA} = \frac{h^2}{m_0 a_0} = \frac{1}{3} t_1^{(i)} f J_x; J_y g \quad (z \quad z): \quad (27)$$

Here z_i are coordinates of the left (i = L) and the right (i = R) interfaces, a_0 is the lattice constant, and $J_{x,y}$ are the operators of angular m om entum 3=2. The heavylight hole mixing coe cients at two interfaces of A $_3$ B $_5$ QW s are related by

$$t_{1\ h}^{(L\)}=\qquad t_{1\ h}^{(R\)}$$
 :

The BIA -contribution for holes in the bulk is described by the H am iltonian 26,35

$$H_{BIA} = \frac{4}{3}c_{1}K V + c_{3}[J_{x}K_{x}(K_{y}^{2} K_{z}^{2}) (28)$$

$$+ J_{y}K_{y}(K_{z}^{2} K_{z}^{2}) + J_{z}K_{z}(K_{x}^{2} K_{y}^{2})];$$

Here c_1 and c_3 are the relativistically-small and non-relativistic valence-band spin-orbit constants, respectively, K = (k; id=dz) is the three-dimensional wave vector, and $V_x = fJ_x; (J_y^2 - J_z^2)g$ etc. In Eq. (28) we neglected the cubic in K relativistically-small terms.

In the basis $jl_h i$, $jl_h i$ both H am iltonians (27) and (28) have the form of Eq. (3) with

$$_{x} + i_{y} = B_{1} \exp(5i_{k}) + B_{2} \exp(i_{k});$$
 (29)

where

The splitting is given by

$$q = 2 B_1^2 + B_2^2 + 2B_1B_2 \cos 4_k :$$

It is seen from Eq. (30) that IIA and BIA give additive contributions to the spin-orbit interaction: the coefcients $B_{1;2}$ have the terms proportional to $t_{1\ h}^{(i)}$ and to $c_{1;3}$. At k! 0 for the h1 subband B_1 k^5 , B_2 k.

 $\ensuremath{\mathtt{C}}$ alculating the photocurrent, we arrive at the expression

$$j_{i}(!) = P_{circ} \frac{e}{h} \frac{epA_{0}}{m_{0}hc}^{2}$$

$$h \lim_{li} (k_{!})G_{1}(k_{!}) + \lim_{li} (k_{!})G_{2}(k_{!}) \delta_{1};$$
(31)

The k-dependent tensors are given by

$$_{xx}^{(1;2)}(k) = _{yy}^{(1;2)}(k) = \frac{dB_{1;2}}{dk}$$
 (32)

and

$$G_{1;2}(k) = \frac{k}{1;2(k)v(k)} \frac{d}{dk} \frac{F_{1;2}(k)u(k)}{v(k)} + \frac{F_{1;2}(k)}{v(k)} \frac{u(k)}{v(k)} \frac{1 + 1;2(k)}{v(k)} :$$
(33)

Here u and v are de ned by Eq. (17) with = 1 and interchange $_{e}$ \$ $_{h}$; $_{1;2}$ = d $\ln B_{1;2}$ =d $\ln k$,

$$_{1}(k) = 5 = _{1}(k);$$
 $_{2}(k) = 1 = _{2}(k);$ (34)

$$F_1 = k (N Q)^2 h W^{3=2} = 1=2;$$
 (35)
 $F_2 = k (N Q)^2 h W^{3=2} = 1=2:$

The upper (lower) sign should be taken for transitions to the odd (even) electron subbands.

At the absorption edge we have the linear law

$$j_{BIA}$$
 h! g^{W} : (36)

The edge behavior of the photocurrent excitation spectra Eqs. (26), (36) are opposite to the electron case. The reason is in the complicated valence band structure. For example, the parabolic behavior (26) contrasts to the electron one Eq. (19) due to the k^2 -dependence of the tensor $_{\rm B\,IA}$ for holes, Eq. (23).

V. RESULTS AND DISCUSSION

Equations (13) – (18), (23) – (25), and (31) – (35) describe the contributions to the circular photocurrent due to interband optical transitions. It is seen that the symmetry of the system determines the direction of the current. Indeed, according to Eq. (14), j_i (!) / j_i 01, i.e. (i) the current appears only under oblique light incidence in (001)-grown QW s, and (ii) for SIA the current j is perpendicular to 0, while for BIA the angle between j and 0 is twice larger than the angle between the axis [100] and 0, see Fig. 1.

The spectrum of the photocurrent is determined by the functions G (k_!). Figure 2 presents the partial contributions to this function for both STA and BTA electron spin splittings calculated for a 100-A wide QW with in nitely-high barriers. The interband transitions from the h1, h2, l1 and h3 hole subbands to the ground electron subband e1 are taken into account. The e ective m asses of the electron, heavy- and light-holes are chosen to correspond to GaAs: m_e = 0.067m₀, m_{hh} = 0.51m₀, m_{lh} = 0.082m₀. The momentum relaxation times are assumed to be related by $_{\rm h}$ = 2 $_{\rm e}$ and independent of the carrier energies. 36

The edge behavior of the photocurrent is due to the h1! el transitions. One can see the linear and quadratic raising of the current near the absorption edge in accordance with Eq. (19). At higher energies, the spectra are determined mainly by the h1! el and h2! el transitions. The di erence between BIA and SIA spectra is crucial: although in both cases the current for the h2! el transitions is mainly negative and has a minimum, in the BIA—induced photocurrent these transitions give twice smaller contribution than h1! el, while for SIA—dom inance they give the main contribution.

The total circular photocurrent caused by the four kinds of optical transitions is presented in Fig. 3. The arrows in Fig. 3 indicate the points where the transitions start. One can see that the BIA-induced circular photocurrent has a peak in the spectrum, while in the SIA case the dip is present around the same point. This photon energy corresponds to excitation of carriers with k=2--a, where a is the quantum well width. At this point the h1 and h2 energy dispersions have an anticrossing. This results in a transform ation of the hole wave functions and, hence, substantial changes in the dependence G (k).

The main feature of Fig. 3 is that the BIA-photocurrent has no sign change in the given energy domain, while in the SIA-case it has a sign-variable spectrum. This makes possible to determ ine the structure symmetry by means of the photogalvanic measurements.

VI. CONCLUDING REMARKS

The situations are possible when the both SIA and BIA are present. The absolute value of the current in the case

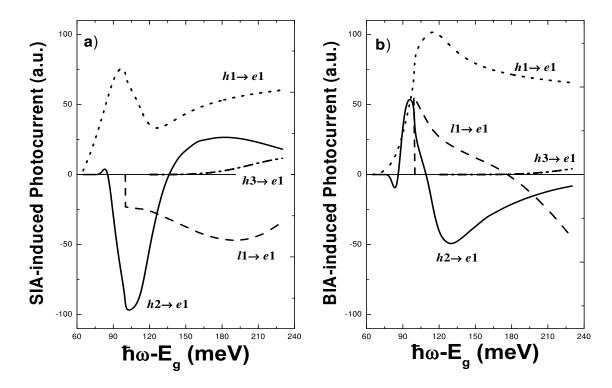


FIG. 2: Partial contributions to the circular photocurrent for direct interband transitions. Spin splitting of the electron states is due to SIA (a) or BIA (b).

$$_{\text{SIA}}$$
 $_{\text{BIA}}$ $\stackrel{\text{6}}{\leftarrow}$ 0 is given by $q = \frac{1}{j_{\text{BIA}}^2 (!) + j_{\text{SIA}}^2 (!)} = \frac{1}{j_{\text{BIA}}^2 (!) + j_{\text{BIA}}^2 (!)} = \frac{1}{j_{\text$

where is the angle between δ and the axis [100]. The upper (lower) sign in Eq. (37) corresponds to $_{B\,IA}$ $_{S\,IA}$ > 0 (< 0). The direction of the photocurrent is given by the angle between [110] and j:

$$\tan = \frac{j_{SIA} (!) + j_{BIA} (!)}{j_{SIA} (!) \quad j_{BIA} (!)} \tan (=4) :$$
 (38)

The angular dependence (37) occurs due to simultaneous presence of Rashba and D resselhaus elds ($_{SIR}$ $_{BIR}$ 6 0) by analogy with the $_k$ -dependence of the spin splitting. It should be noted that j_{SIR} and j_{BIR} have di erent excitation spectra that causes complicated !-dependences of the total photocurrent absolute value and direction, Eqs. (37), (38).

The analysis shows that, under an isotropic scattering, the \interference" terms $_{\rm B\,IA} = (_{\rm B\,IA}^{\,2} + _{\rm S\,IA}^{\,2})$ appear in the total photocurrent Eq. (13) even in the linear in

's regime. This is caused by coupling of the Fourier harmonics of the velocity operator and density matrix in Eq. (5).

In conclusion, we have developed a theory of the interband circular photogalvanice ect in QW s. The cases when either SIA, BIA or IIA dominates have been considered. It is shown that SIA and BIA result in non-equal photocurrents in QW s. Their excitation spectra have absolutely dierent shapes in the whole studied range. This makes the interband circular photogalvanice ect a unique highly sensitive tool for investigation of symmetry and spin properties of QW s.

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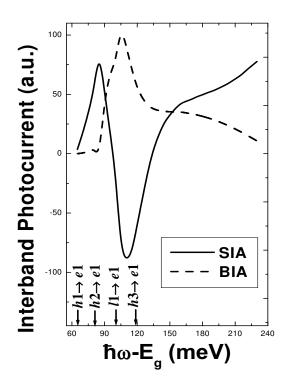


FIG.3: Spectrum of the interband circular photocurrent due to SIA (solid line) and BIA (dashed line) electron spin splittings in a 100-A wide QW. The arrows indicate the absorption edges for the four optical transitions.

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